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TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π -MOSV)

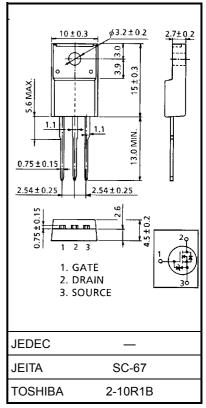
2SK2842

Chopper Regulator, DC–DC Converter and Motor Drive Applications

- Low drain-source ON resistance $R_{DS}(ON) = 0.4 \Omega$ (typ.)
- High forward transfer admittance $|Y_{fs}| = 9.0 \text{ S (typ.)}$
- Low leakage current $: I_{DSS} = 100 \ \mu A \ (max) \ (V_{DS} = 500 \ V)$
- Enhancement-mode $: V_{th} = 2.0 \sim 4.0 \text{ V} (V_{DS} = 10 \text{ V}, \text{I}_{D} = 1 \text{ mA})$

Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Drain-source voltage		V _{DSS}	500	V	
Drain-gate voltage (R _{GS} = 20 kΩ)		V _{DGR}	500	V	
Gate-source voltage		V _{GSS}	±30	V	
Drain current	DC (Note 1)	۱ _D	12	A	
	Pulse (Note 1)	I _{DP}	48	А	
Drain power dissipatio	n (Tc = 25°C)	PD	40	W	
Single pulse avalanche energy (Note 2)		E _{AS}	364	mJ	
Avalanche current		I _{AR}	12	А	
Repetitive avalanche energy (Note 3)		E _{AR}	4.0	mJ	
Channel temperature		T _{ch}	150	°C	
Storage temperature range		T _{stg}	-55~150	°C	



Weight: 1.9 g (typ.)

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	R _{th (ch−c)}	3.125	°C / W
Thermal resistance, channel to ambient	R _{th (ch−a)}	62.5	°C / W

Note 1: Please use devices on condition that the channel temperature is below 150°C.

Note 2: V_DD = 90 V, T_ch = 25 $^\circ C$ (initial), L = 4.3 mH, R_G = 25 Ω , I_AR = 12 A

Note 3: Repetitive rating; Pulse width limited by maximum channel temperature.

This transistor is an electrostatic sensitive device. Please handle with caution.

Unit: mm

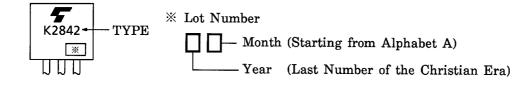
Electrical Characteristics (Ta = 25°C)

Charao	cteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cu	ırrent	I _{GSS}	V_{GS} = ±25 V, V_{DS} = 0 V	_	_	±10	μA
Gate-source bro	eakdown voltage	V (BR) GSS	$I_{G} = \pm 10 \ \mu A, V_{DS} = 0 \ V$	±30	_	_	V
Drain cut-off cu	rrent	I _{DSS}	V _{DS} = 500 V, V _{GS} = 0 V	_	_	100	μA
Drain-source br voltage	reakdown	V _(BR) DSS	I _D = 10 mA, V _{GS} = 0 V	500	_	_	V
Gate threshold v	/oltage	V _{th}	V _{DS} = 10 V, I _D = 1 mA	2.0	_	4.0	V
Drain-source O	N resistance	R _{DS (ON)}	V _{GS} = 10 V, I _D = 6 A	_	0.4	0.52	Ω
Forward transfe	r admittance	Y _{fs}	V _{DS} = 10 V, I _D = 6 A	4.0	9.0	_	S
Input capacitance	e	C _{iss}			2040	_	pF
Reverse transfer capacitance		C _{rss}	V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz	_	200	_	
Output capacitance		C _{oss}		_	640	_	
Switching time	Rise time	tr	$- \frac{V_{GS} \stackrel{10V}{_{0V}} \int_{U} \int_{U} \int_{R_L} V_{OUT}}{V_{OUT}}$ $- \frac{V_{GS} \stackrel{10V}{_{0V}} \int_{U} \int_{R_L} V_{OUT}}{V_{DD} \Rightarrow 200V}$ $- \frac{V_{DD} \Rightarrow 200V}{Duty \le 1\%, t_w = 10\mu s}$	_	22	_	
	Turn-on time	t _{on}		_	58	_	20
	Fall time	t _f		_	36	_	ns
	Turn-off time	t _{off}		_	180	_	
Total gate charge (gate-source plus gate-drain)		Qg		_	45	_	
Gate-source charge		Q _{gs}	V _{DD} ≈ 400 V, V _{GS} = 10 V, I _D = 12 A		25	_	nC
Gate-drain ("miller") Charge		Q _{gd}			20	_	

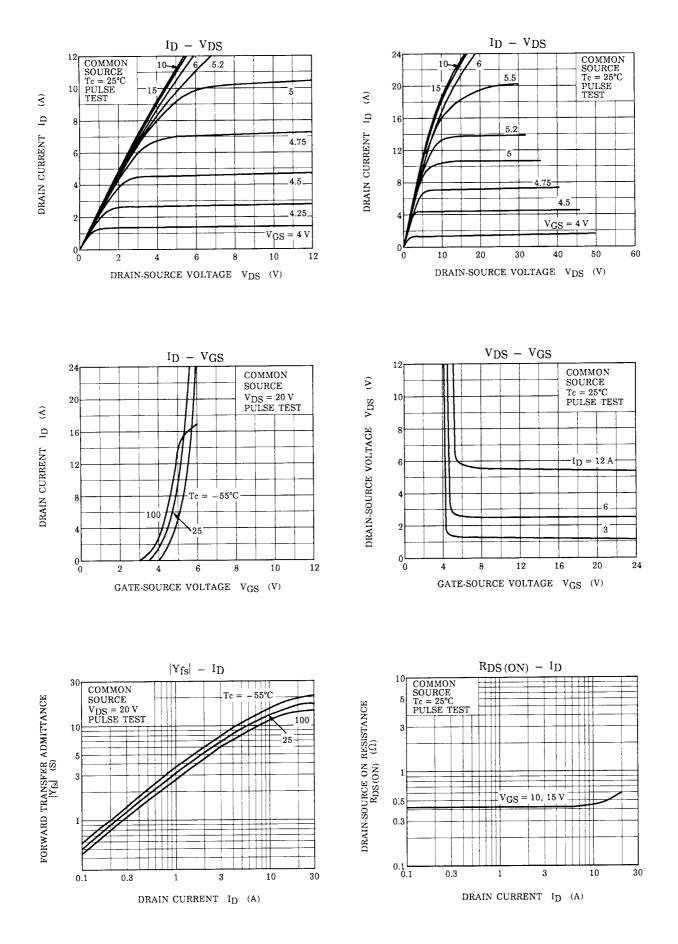
Source–Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I _{DR}	_	_	_	12	А
Pulse drain reverse current (Note 1)	I _{DRP}	—	_	_	48	А
Forward voltage (diode)	V _{DSF}	I _{DR} = 12 A, V _{GS} = 0 V	_	_	-1.7	V
Reverse recovery time	t _{rr}	I _{DR} = 12 A, V _{GS} = 0 V dI _{DR} / dt = 100 A / μs		1200		ns
Reverse recovery charge	Q _{rr}	dI _{DR} / dt = 100 A / μs	_	16	_	μC

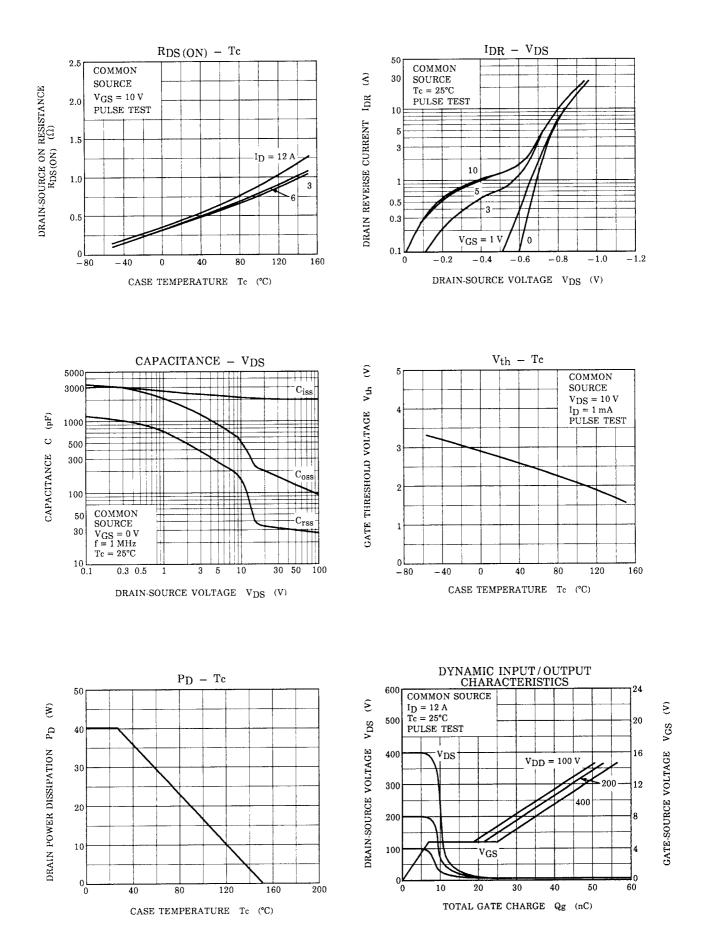
Marking



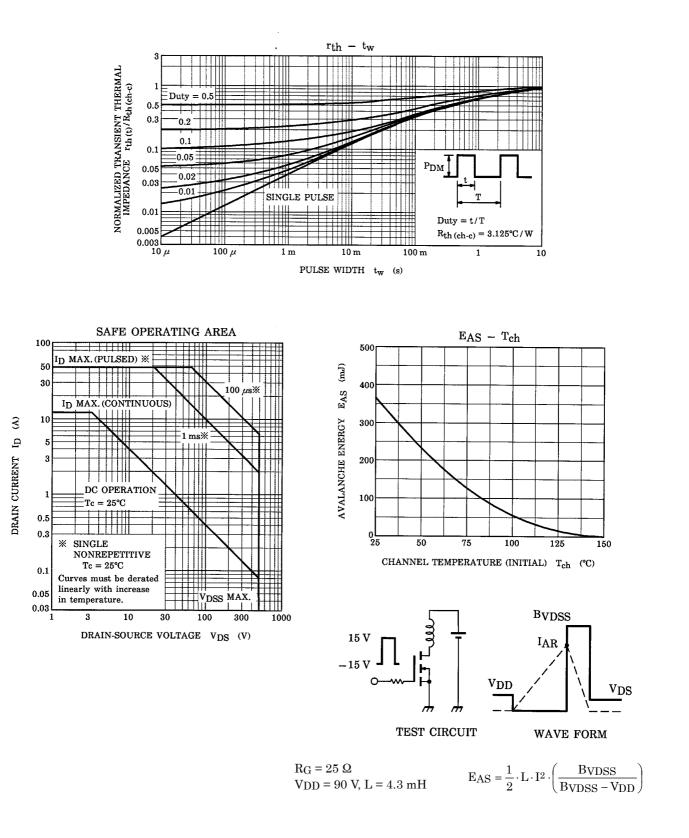
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